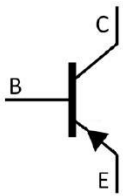


Silicon PNP transistor in a TO-92 Plastic Package.

Complement to KSC815.

Low frequency power amplifier applications.

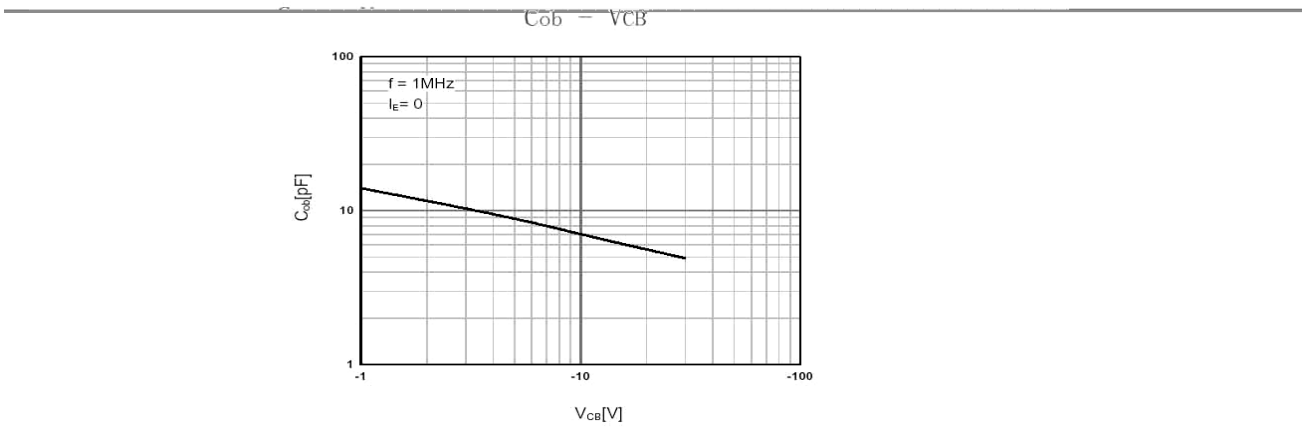
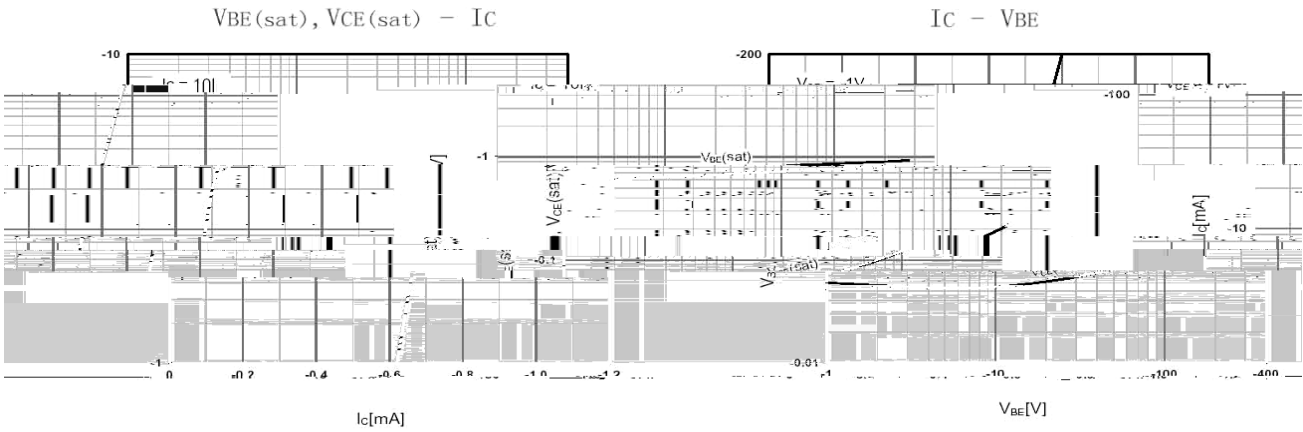
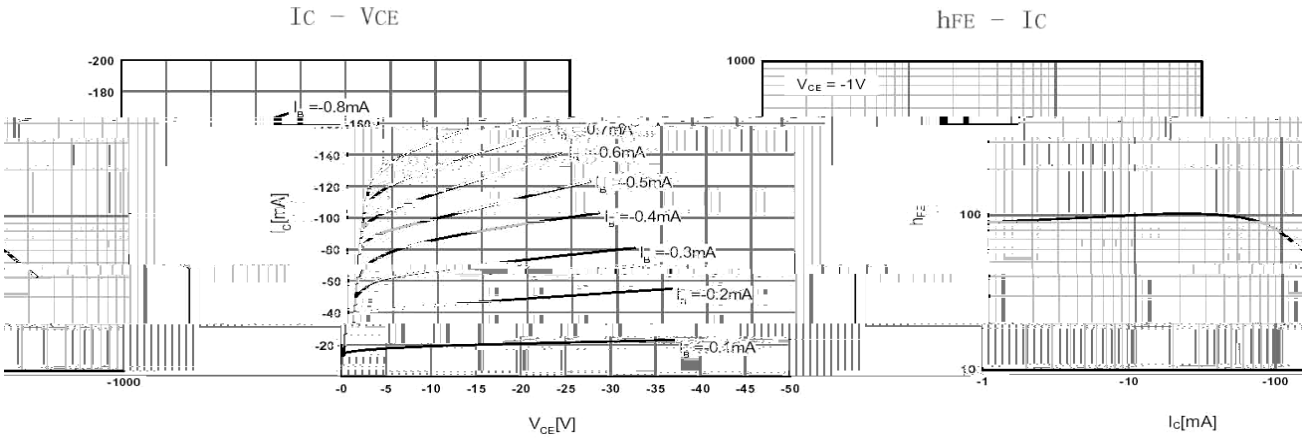


PIN1 Collector PIN 2 Base PIN 3 Emitter

h_{FE} Classifications Symbol	R	O	Y
h_{FE} Range	40~80	70~140	120~240

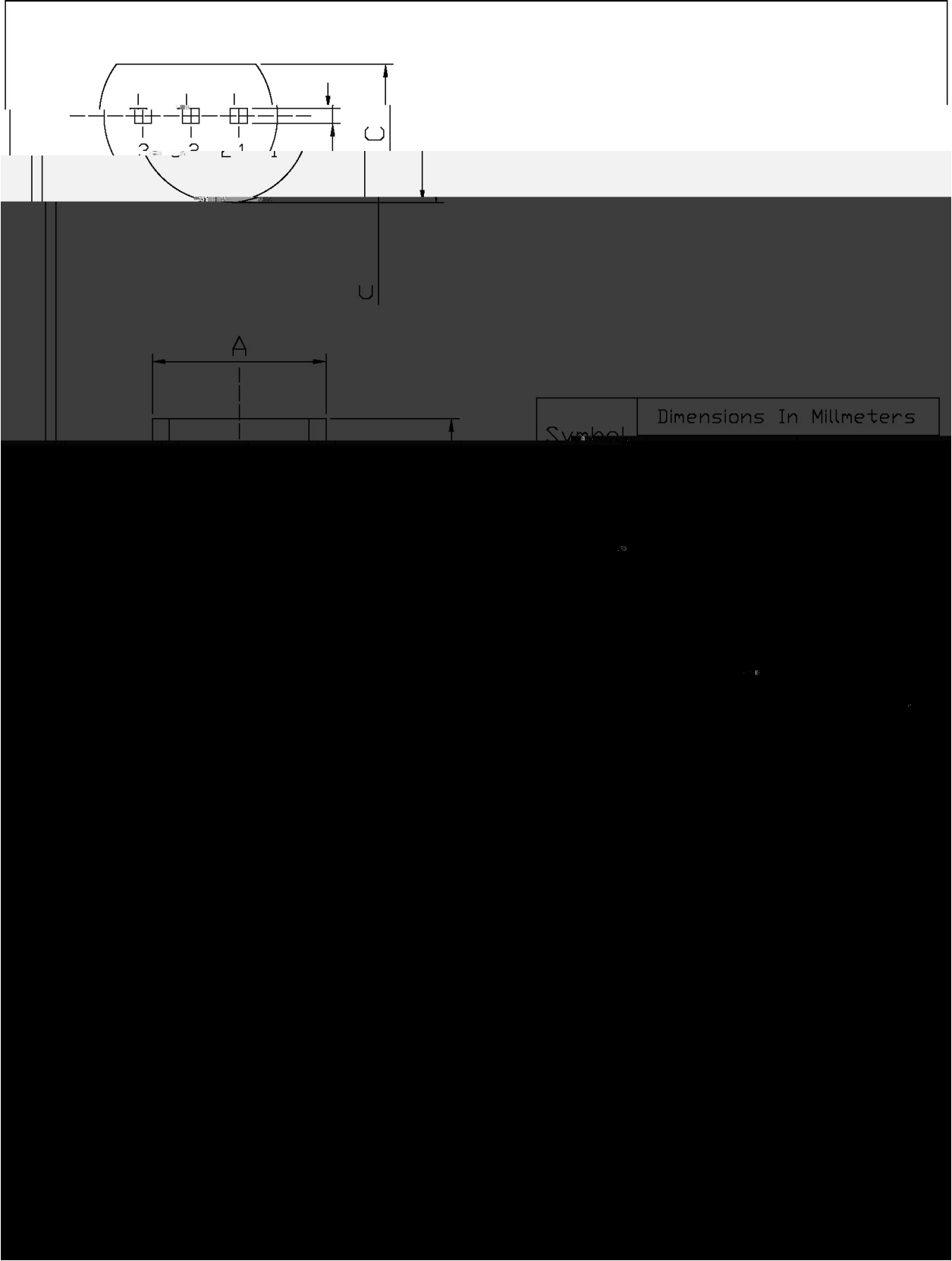
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-45	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-200	mA
Collector Power Dissipation	P_C	400	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55~150	

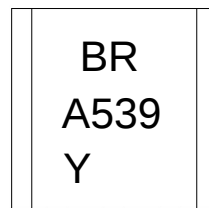
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=-100\mu A$ $I_E=0$	-60			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-10mA$ $I_B=0$	-45			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=-10\mu A$ $I_C=0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-45V$ $I_E=0$			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-3.0V$ $I_C=0$			-0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=-1.0V$ $I_C=-50mA$	40		240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-150mA$ $I_B=-15mA$		-0.25	-0.5	V
Base -Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-150mA$ $I_B=-15mA$		-0.9	-1.2	V
Base -Emitter Voltage	V_{BE}	$V_{CE}=-1.0V$ $I_C=-10mA$	-0.60	-0.65	-0.90	V



T0-92

Unit: mm





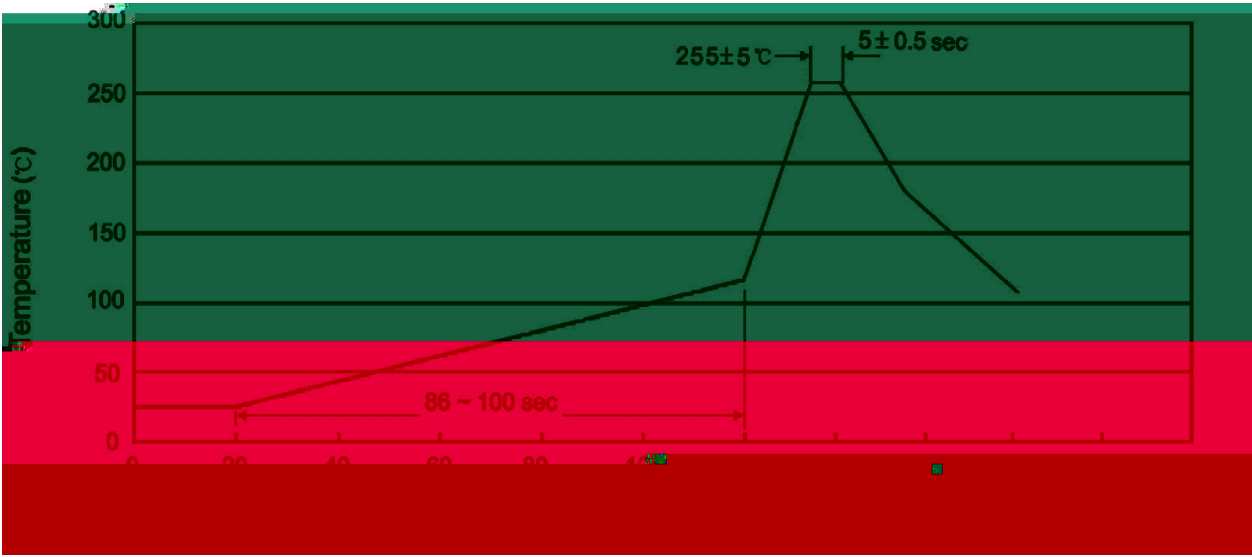
Note:

BR: Company Code.

A539: Product Type.

Y: h_{FE} Classifications Symbol

***: Lot No. Code, code change with Lot No.



Note:

- 1

25 150

60 90sec;
- 2

255 5

5 0.5sec;
- 3

2 10

/sec.
- 1.Preheating:25~150

, Time:60~90sec.
- 2.Peak Temp.:255 5

, Duration:5 0.5sec.
3. Cooling Speed: 2~10

/sec.

270 5

10 1 sec.

Temp:270±5

Time:10±1 sec

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	只 袋	袋 盒	只 盒	盒 箱	只 箱	袋	盒	箱

/ AMMO

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)	
	只 纸带	纸带 盒	纸带层 盒	盒 箱	只 箱	盒	箱
							小箱 , 大箱